

L Number	Hits	Search Text	DB	Time stamp
-	7	y\$1branch and corner same (etch\$4 or mask\$4 or photo\$1resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 10:38
-	22	corner near8 (etch\$4 or mask\$4 or photo\$1resist) near5 sharp\$4 same isotropic and 438/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 10:58
-	3	y\$1branch\$3 and (sharp\$4 near5 corner) same (etch\$4 or mask\$4 or pattern\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 11:00
-	3	y\$1branch\$3 and (sharp\$4 near5 corner) same (etch\$4 or mask\$4 or pattern\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 11:01
-	9	leon.in. and etch\$4 same corner\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 11:01
-	1	y\$1branch\$3 and (etch\$4 near6 corner) and (cmp or polish\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 11:41
-	3	y\$1branch\$3 and (etch\$4 near6 corner)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 11:54
-	99	(etch\$4 near6 corner) near10 isotropic\$4 and 438\$5.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 13:17
-	14	(sharpen\$3 near6 corner) same etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 13:30
-	9	(sharpen\$3 near6 corner) and 438\$5.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/10 13:32
-	2	5521422.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 10:12
-	33	leon.in. and francisco.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 10:17
-	18	438/25.ccls. and corner\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 10:34
-	14	438/25.ccls. and sharp\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/14 10:36

-	73	y\$1branch\$4 same (etch\$4 or mask\$4) and waveguide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/14 10:39
-	64	y\$1branch\$4 same etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/18 16:44
-	64	y\$1branch\$4 same etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/18 17:01
-	6	y\$1branch\$4 same etch\$4 and (chemical near3 polish\$4 or cmp)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/18 16:46
-	33	LEON.in. and FRANCISCO.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/18 17:02
-	86	LEON near2 FRANCISCO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/18 17:02
-	21	(LEON near2 FRANCISCO).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/18 17:03
-	2	((LEON near2 FRANCISCO).in. or (everett near2 wang).in.) and grat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/18 17:04
-	22	(LEON near2 FRANCISCO).in. or (everett near2 wang).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/18 17:09
-	47	diffract\$4 near2 grat\$4 same etch\$4 same monit\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/19 10:12
-	55	grat\$4 same etch\$4 near10 monit\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/19 10:49
-	11	trench near4 fill\$4 same (cmp or chemical near2 (polish\$4 or planar\$5)) same deposit\$4 and 438/\$4.ccls. and (photonic or mems or y\$1branch)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/19 11:47
-	70	trench near4 fill\$4 near4 (nitride) same (cmp or chemical near2 (polish\$4 or planar\$5)) same deposit\$4 and 438/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/19 12:18
-	5	trench near4 fill\$4 same (cmp or chemical near2 (polish\$4 or planar\$5)) same deposit\$4 same core and 438/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/19 12:20

-	2	trench near4 fill\$4 same (cmp or chemical near2 (polish\$4 or planar\$5)) same deposit\$4 and 438/\$4.ccls. and (core same clad\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 12:25
-	11	trench near4 fill\$4 same (cmp or chemical near2 (polish\$4 or planar\$5)) same deposit\$4 and 438/\$4.ccls. and waveguide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 12:30
-	0	fill\$4 near4 nitride same (cmp or chemical near2 (polish\$4 or planar\$5)) same deposit\$4 and 438/\$4.ccls. and waveguide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 12:32
-	128	fill\$4 near4 nitride same (cmp or chemical near2 (polish\$4 or planar\$5)) same deposit\$4 and 438/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 12:47
-	1	fill\$4 same (cmp or chemical near2 (polish\$4 or planar\$5)) same deposit\$4 and 438/\$4.ccls. and y\$1branch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 12:48
-	33	fill\$4 same (cmp or chemical near2 (polish\$4 or planar\$5)) same deposit\$4 and 438/\$4.ccls. and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 12:49
-	23	("4307180" "4786954" "4849344" "5173439" "5272117" "5296392" "5297082" "5346587" "5433794" "5436488" "5459096" "5492858" "5506168" "5516625" "5516721" "5521422" "5677233" "5683932" "5712185" "5801083" "5811346" "5834358" "5960297").PN.	USPAT	2003/03/19 13:21
-	27	trench near2 isolation near2 structure same oxide near5 overly\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 15:15
-	1	RCA\$1A near10 HF	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 15:16
-	1	RCA\$1A same HF	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 15:16
-	12	RCA\$1A	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 15:17
-	26	(HF near10 (clean\$3 or pre\$1clean\$3) same trench) and (STI or shallow\$1trench)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 17:06
-	2	5521422.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/19 16:07

-	75	isotropic same corner same etch\$4 same sharp\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/19 16:08
-	84	(STI or shallow\$trench) and MEMS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/19 17:06
-	9	(STI or shallow\$trench) same MEMS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/19 17:06
-	1	(STI or shallow\$trench) same MEMS!	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/19 17:07
-	5	(STI or shallow\$trench) and MEMS!	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/19 17:08
-	27	(STI or shallow\$trench) and waveguide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/19 17:11
-	82	(STI or shallow\$trench or shallow adj trench) and waveguide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 09:53
-	17	(STI or shallow\$trench or shallow adj trench) same waveguide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/19 17:11
-	0	(STI or shallow\$trench or shallow adj trench) and waveguide and (y\$1branch or y adj branch)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/19 17:33
-	5	(STI or shallow\$trench or shallow adj trench) same (mems! or microelectromechanical)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 10:35
-	105	corner same etch\$4 near4 wet and optical\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 10:57
-	92	corner same etch\$4 near4 wet same sharp\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 11:10
-	75	etch\$4 near4 (wet or isotropic) and y adj branch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:45
-	41	etch\$4 near4 (wet or isotropic) same (dry or anisotropic) and y adj branch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 11:18

-	1	y adj branch\$4.ti. and (wet near4 etch\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 11:19
-	1	y adj branch\$4.ti. and 438\$5.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 11:21
-	61	y adj branch\$4 near15 (mask\$4 or pattern\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 13:34
-	30	y adj branch\$4 near35 etch\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 11:58
-	6	y adj branch\$4 near35 sharp\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:42
-	6	y adj branch\$4 near35 clean\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:44
-	53	corner and y adj branch\$4 and optical	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:46
-	6	corner same etch\$4 and y adj branch\$4 and optical	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:50
-	68	corner near10 etch\$4 near5 (wet or isotropic) same (photoresist or resist or mask\$4) and 438/\$5.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 12:58
-	10	y adj branch\$4 near15 (photoresist or resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 13:42
-	10	y adj branch\$4 same corner	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 13:37
-	30	y adj branch\$4 near35 etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 14:19
-	84	y adj branch\$4 near5 waveguide and etch\$4 same cladding	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 14:23
-	12	y adj branch\$4 near5 waveguide and etch\$4 same cladding and (chemical near2 mechanical or cmp)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 14:52

-	32	cladding near20 etch\$4 near4 wet same core and waveguide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 15:04
-	84	(shallow adj trench or sti) and waveguide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 15:05
-	17	(shallow adj trench or sti) same waveguide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 16:06
-	33	waveguide near10 y adj branch\$4 same etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 16:10